

Program

(status as of February 11, 2025)

Thursday, May 22

12:00: *Welcome and lunch*

- 14:00 – 14:15: **Welcome and introduction**, Andreas Erdmann (Fraunhofer IISB)
- 14:15 – 14:40: **Physics is all you need: Self-supervised learning for inverse lithography**, Hans-Christian Ruiz (ASML)
- 14:40 – 15:05: **DNN based approaches for EUV mask inspection**, Paolo Ansuinelli, Suman Saha, Luis Felipe Barba Flores, Benjamín Béjar Haro, Yasin Ekinci, Iacopo Mochi (PSI)
- 15:05 – 15:30: **AIMS[®] EUV: A holistic approach to EUV mask qualification**, Matthias Roesch, Maximilian Albert, Grizelda Kersteen, Andreas Verch, Klaus Gwosch, Renzo Capelli (Zeiss SMT)

15:30 – 16:00: *Coffee break*

- 16:00 – 16:25: **Kinetic modeling of radical inhibition in tomographic volumetric 3D printing**, Quinten Thijssen, Antonio Jaén Ortega, Roniérik Pioli Vieira, Sandra Van Vlierberghe (Ghent University)
- 16:25 – 16:50: **Recent computational advances in tomographic volumetric additive manufacturing**, Felix Wechsler, Viola Sgarminato, Christophe Moser (EPFL, Lausanne)
- 16:50 – 17:15: **Accelerating the characterization of nanostructures through novel forward simulations and neural network approaches**, Vinh-Binh Truong¹, Analia Fernandez Herrero¹, Philipp Hönicke², Victor Soltwisch² (¹PTB, ²HZB)

17:30: *Poster session*

18:30: *Dinner*

- 20:00 – 20:20: **20 years Fraunhofer Simulation Workshop**
- 20:20 – 21:10 pm: **Keynote**: Patrick Naulleau (EUV Tech Inc. and Berkeley Lab)

Friday, May 23

- 9:00 – 9:25: **An eigendecomposition-free RCWA implementation for high-performance parallel computing**, Frank van der Ceelen, Yifeng Shao, Wim Coene (TU Delft)
- 9:25 – 9:50: **Rigorous electromagnetic simulation for EUV lithography and CNN reproducing electromagnetic simulations**, Hiroyoshi Tanabe, Masayuki Shimoda and Atsushi Takahashi (Institute of Science Tokyo)
- 9:50 – 10:15: **Physics-informed deep learning for 3D modeling of light diffraction from optical metasurfaces**, Vlad Medvedev (Fraunhofer IISB)

10:15 – 10:45: *Coffee break*

- 10:45 – 11:10: **Multiphoton absorption polymerization: Fundamentals, kinetics, and potential alternatives**, John T. Fourkas, John S. Petersen, Nicholas Fisher, Nikos Liaros, Mac Cohen, Sandra Gutierrez-Razo, Anders Dollard, and Julio Argueta (Univ. of Maryland)

- 11:10 – 11:35: **Physics-based deep learning network for inverse lithography in two-photon polymerization**, Valeriia Sedova¹, Thomas Le Deun², Joël Rovera², Jonas Wiedenmann³, Kevin Heggarty², Andreas Erdmann¹ (¹Fraunhofer IISB, ²IMT Atlantique, ³Heidelberg Instruments Mikrotechnik GmbH)
- 11:35 – 12:00: **A machine learning approach to structure precompensation in 3D μ -printing**, Sven Enns, Nicholas Lang, Julian Hering-Stratemeier, Georg von Freymann (RPTU Kaiserslautern, Fraunhofer ITWM)

12:00: Lunch

- 13:30 – 13:55: **EUV diffraction orders and absorber dielectric index: comparison of analytical and simulation approach**, Martin Burkhardt, Rajiv Sejpal (IBM Research)
- 13:55 – 14:20: **Mask absorber impact on local MEEF for pitch 32 nm hexagonal contact hole printing with low-n EUV masks**, Andreas Frommhold, Vicky Philipsen (imec)
- 14:20 – 14:45: **High NA Stitching: Model and OPC assessment by using low-n mask**, Dongbo Xu¹, Qinglin Zeng¹, Xuefeng Zeng¹, Werner Gillijns², Shibing Wang¹, Germain Fenger¹ (¹Siemens EDA, ²imec)
- 14:45 – 15:10: **Efficient aerial image simulations of rotated 1D patterns in anamorphic systems for lens aberration reconstruction from in-resist measurements**, Bas van Meerten, Dennis Stoel, Hilbert van Loo, Laurens de Winter (ASML)

15:30 pm: Special event and dinner

Saturday, May 24

- 9:00 – 9:25: **Modeling and characterization of EUV resists**, Takahiro Kozawa (SANKEN, Osaka University)
- 9:25 – 9:50: **Multi-trigger resists: Modeling and simulation results**, Thiago J. dos Santos¹, Andreas Erdmann¹, Alex P. G. Robinson^{2,3}, Alexandra McClelland², Carmen Popescu², Bernardo Oyarzún⁴, Joost van Bree⁴, and Mark van de Kerkhof⁴ (¹Fraunhofer IISB, ²Irresistible Materials, ³University of Birmingham, ⁴ASML)
- 9:50 – 10:15: **Tuning resist profile and pattern variability with depth of focus and absorption**, Christoph Hauenstein¹, Bernardo Oyarzun Rivera¹, Luc van Kessel¹, Joost van Bree¹, Ruben Maas¹, Vincent Renaud², Tatiana Kovalevich², Bhavishya Chowrira² (¹ASML, ²IMEC)

10:15 – 10:45: Coffee break

- 10:45 – 11:10: **Inverse mask design for displacement Talbot lithography**, Zhixin Wang, Stefan Rietmann, Li Wang, Harun H. Solak (Eulitha)
- 11:10 – 11:35: **From physics-based optimization to augmented deep learning optimization in grayscale photolithography**, Mask Merlin Moreau, Jean-Baptiste Henry, Stéphane Bonnet (Univ. Grenoble Alpes, CEA, Leti)
- 11:35 – 12:00: **Modeling spectral behavior of grayscale lithography for broadband imaging and display**, Aamod Shanker^{1,2}, Arka Majumdar¹, Diogo Aguiam² (¹University of Washington, ²Iberian Nanotechnology Laboratory)
- 12:00 – 12:10: **Concluding remarks**

12:30: Lunch